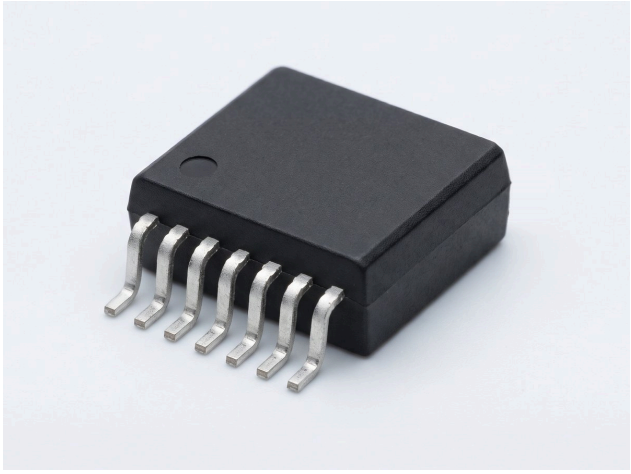
IHSD12R030D7

1200 V, 30 mΩ, Silicon Carbide, Single switch

V_{DSS}	**1200 V**
$R_{DS(on)}$	**30 mΩ**



D2PAK-7

Features

- Kelvin-source pin
- Surface-mount D2PAK-7 for automated assembly

Typical applications

- On-board chargers
- Server and telecom power supplies
- Solar optimisers and string inverters

Description

1200 V, 30 mΩ silicon-carbide MOSFET in a D2PAK-7 package with Kelvin source.

Key specifications

Parameter	Value
V_{DSS}	1200 V
$R_{DS(on)}$ typ., V_{GS} = 18 V, T_{vj} = 25 °C	30 mΩ
I_D, T_C = 25 °C	75 A
Recommended $V_{GS(on)}$	18 V

Full characterization data

Thermal resistance, switching energies and times, capacitances, gate charge and typical characteristic curves for IHSD12R030D7 are available on request: request the full data or write to sales@ironhawksemi.com.

Package

D2PAK-7. Mechanical outline drawing, STEP model and PCB footprint available on request.

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Ordering information

Part number	Packing	MOQ	Lead time
IHSD12R030D7	Tape & reel	On request	On request

Information in this document is believed to be accurate but is subject to change without notice. Typical values are not guaranteed. The customer is responsible for validating suitability in the end application. IRONHAWK · sales@ironhawksemi.com

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